



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	RDS(ON) max	I _{D MAX} T _A = +25°C
	$59mΩ @ V_{GS} = -4.5V$	-3.9A
-12V	$81m\Omega$ @ $V_{GS} = -2.5V$	-3.3A
	115mΩ @ V _{GS} = -1.8V	-2.8A

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Power Management Functions
- Portable Power Adaptors

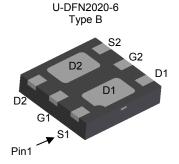
Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- ESD protected gate.
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

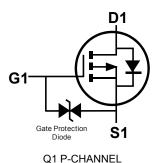
Mechanical Data

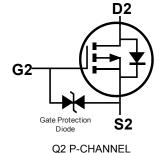
- Case: U-DFN2020-6 Type B
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (approximate)





Bottom View





Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP1055UFDB -7	U-DFN2020-6 Type B	3000/Tape & Reel
DMP1055UFDB -13	U-DFN2020-6 Type B	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



D6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	2012	2	2013		2014	20	15	2016		2017	2	2018
Code	Z		Α		В	(D		Е		F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	-12	V	
Gate-Source Voltage		V_{GSS}	±8	V	
Continuous Drain Current (Note E) V = 4 EV	Steady State	T _A = +25°C T _A = +70°C	l _D	-3.9 -3.1	А
Continuous Drain Current (Note 5) V _{GS} = -4.5V	t < 5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-5.0 -4.0	А
Maximum Continuous Body Diode Forward Curre	Is	-1.7	Α		
Pulsed Drain Current (10µs pulse, duty cycle = 1	%)	I_{DM}	-25	A	

Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 5)	Steady State	р	1.36	W	
Total Power Dissipation (Note 5)	t < 5s	P_{D}	1.89		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	92		
Thermal Resistance, Junction to Ambient (Note 5)	t < 5s	$R_{\theta JA}$	66	°C/W	
Thermal Resistance, Junction to Case (Note 5)	$R_{ heta JC}$	18			
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

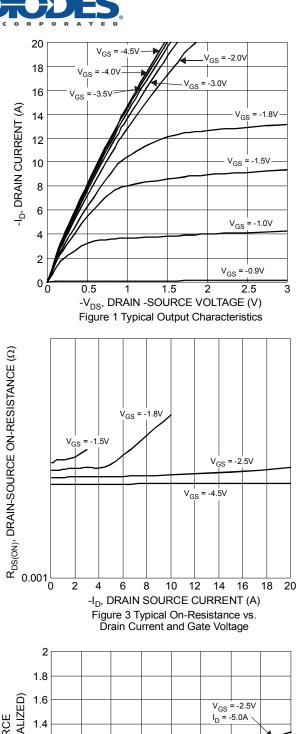
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

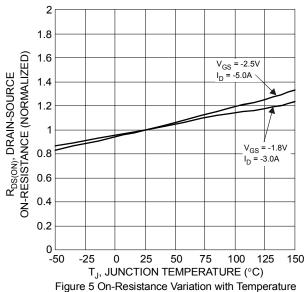
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	-12	l	l	٧	$V_{GS} = 0V$, $I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	l	I	-1.0	μΑ	$V_{DS} = -12V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	l	l	±10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-0.4	_	-1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			37	59		$V_{GS} = -4.5V$, $I_{D} = -3.6A$
Static Drain-Source On-Resistance	D	l	48	81	mΩ	$V_{GS} = -2.5V$, $I_D = -3.1A$
Static Drain-Source On-Resistance	R _{DS} (ON)		69	115	11177	$V_{GS} = -1.8V$, $I_D = -2.6A$
		_	88	215		$V_{GS} = -1.5V, I_D = -0.5A$
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -3.7A$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	l	1028	l	pF	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Output Capacitance	Coss		285	_	pF	$V_{DS} = -6V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C_{rss}	_	254	_	pF	1 - 1:01/11/12
Gate Resistance	R_g	_	19.6	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)		_	13	_	nC	
Total Gate Charge (V _{GS} = -8V)	Qg	_	20.8	_	nC	1 401/ 1 474
Gate-Source Charge	Q_{gs}	_	1.8	_	nC	$V_{DS} = -10V, I_D = -4.7A$
Gate-Drain Charge	Q _{qd}	_	4.5	_	nC	1
Turn-On Delay Time	t _{D(on)}		5.6	_	ns	
Turn-On Rise Time	t _r		12.8	_	ns	$V_{DD} = -6V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(off)}	_	30.7	_	ns	$R_L = 1.6\Omega$, $R_G = 1\Omega$
Turn-Off Fall Time	t _f		25.4	-	ns	1
Body Diode Reverse Recovery Time	trr		31.6	_	nS	$I_S = -3.6A$, $dI/dt = 100A/\mu s$
Body Diode Reverse Recovery Charge	Qrr	_	7.8	_	nC	$I_S = -3.6A$, $dI/dt = 100A/\mu s$

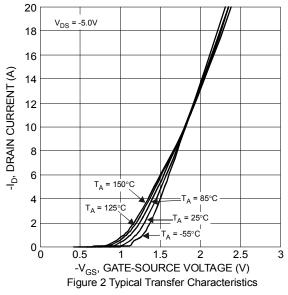
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.6. Short duration pulse test used to minimize self-heating effect.

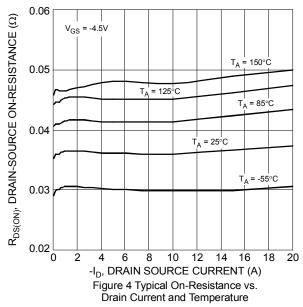
^{7.} Guaranteed by design. Not subject to product testing.











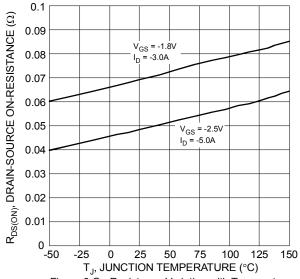


Figure 6 On-Resistance Variation with Temperature



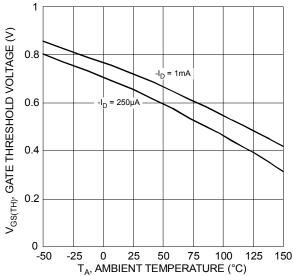
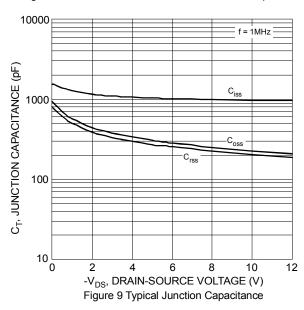
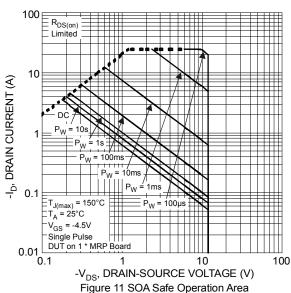
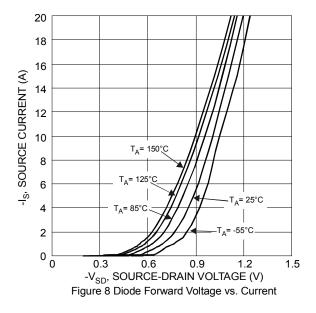
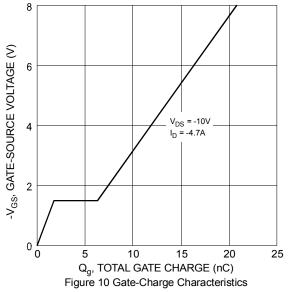


Figure 7 Gate Threshold Variation vs. Ambient Temperature

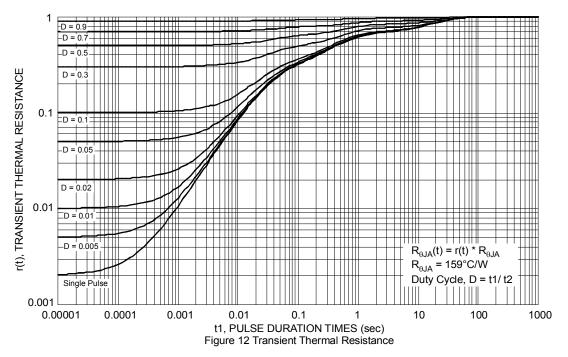






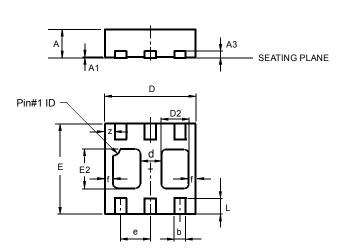






Package Outline Dimensions

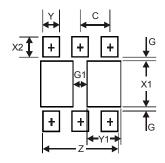
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



U-DFN2020-6								
Type B								
Dim	Min	Max	Тур					
Α	0.545	0.605	0.575					
A1	0	0.05	0.02					
A3			0.13					
b	0.20	0.30	0.25					
D	1.95	2.075	2.00					
d			0.45					
D2	0.50	0.70	0.60					
е			0.65					
E	1.95	2.075	2.00					
E2	0.90	1.10	1.00					
f			0.15					
L	0.25	0.35	0.30					
z			0.225					
All Dimensions in mm								

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
Z	1.67			
G	0.20			
G1	0.40			
X1	1.0			
X2	0.45			
Υ	0.37			
Y1	0.70			
С	0.65			



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